

CLAIMS

1. A method of testing comprising:
 - disposing a first film of a first contact material on a substrate;
 - disposing a second film of a second contact material on a rounded end piece,
 - wherein a radius of curvature of the rounded piece along a contact surface between the first film and the second film is higher than 10 μm and lower than 100 μm ; and
 - measuring a characteristic related to the first film and the second film contacting using at least one measurement circuit to perform at least one measurement after the first film and the second film contact each other at a controlled force.
2. The method according to claim 1 wherein the step of measuring the characteristic related to the first film and the second film contacting occurs when the first film and the second film contact with the controlled force not exceeding 10 μN .
3. The method according to claim 2 wherein the characteristic is a contact resistance value.
4. The method according to 1 wherein the characteristic is a current-dependent stiction force value and wherein the step of measuring the characteristic related to the first film and the second film contacting occurs after the first film and the second film contact with the controlled force and while the first film and the second film contact with a stiction measurement force not exceeding 1 mN.

5. The method of claim 4 wherein the step of measuring the current-dependent stiction force value is performed after passing a current higher than 5 μA and lower than 100 μA through a contact interface between the first film and the second film when the first film and the second film contact with the controlled force.